# **PNP Medium Power Transistor (Switching)**

UMT2907A / SST2907A/MMST2907A / RXT2907A / PN2907A

#### Features

- 1) BVcEo<-40V (Ic=-10mA)
- Complements the UMT2222A/SST2222A/MMST2222A/ RXT2222A/PN2222A.

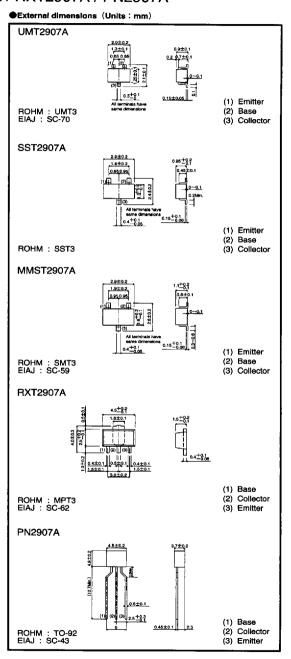
#### Package, marking and packaging specifications

Туре	UMT2907A	SST2907A	MMST2907A	RXT2907A	PN2907A
Package	UMT3	SST3	SMT3	MPT3	TO-92
Marking	R2F	R2F	R2F	AC*	_
Code	T106	T116	T146	T100	T93
Basic ordering unit (pieces)	3000	3000	3000	1000	3000

<sup>\*</sup> Indicates lot number.

#### ●Absolute maximum ratings (Ta=25℃)

Para	meter	Symbol	Limits	Unit
Collector-base vi	oltage	Vcвo	-60	V
Collector-emitter	voltage	VCEO	60	V
Emitter-base volt	age	VEBO	-5	V
Collector current		Ic	-0.6	Α
Collector power dissipation	UMT2907A, SST2907A, MMST2907A	Pc	0.2	w
o.oo.panon	RXT2907A	1	0.5	
	PN2907A	1	0.625	
Junction tempera	ature	Tj	150	Č
Storage tempera	ture	Tstg	-55~150	ů



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#### ●Electrical characteristics (Ta = 25℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	60	_	_	٧	lc=10 μA
Collector-emitter breakdown voltage	BVCEO	60	-		٧	lc=10mA
Emitter-base breakdown voltage	BVEBO	5	_	_	V	l∈=10 μ A
Collector cutoff current	lcso	_		-100		Vc8=-50V
Collector cutoff current	ICES	_	_	-100		Vca=-30V
Emitter cutoff current	lebo	-	_	-100	nA	V⊞=-3V
5. II		_	_	-0.4	v	lc/la=-150mA/-15mA
Collector-emitter saturation voltage	VCE(set)	_		-1.6	١ ٧	Ic/Is=-500mA/-50mA
Dan and make and make	1/	0.6		-1.3	v	lc/le=-150mA/-15mA
Base emitter saturation voltage	VBE(set)	_	_	-2.6	<b>'</b>	lc/ls=-500mA/-50mA
	hre	75	_	_		Vc=-10V, lc=-0.1mA
		100	_	_		Vc=-10V , lc=-1mA
DC current transfer ratio		100	l –	_		Vc=-10V , lc=-10mA
DC current transfer fatto		100		300		Vc=-10V, lc=-150mA
		50		_		Vc=-10V , lc=-500mA
Transition frequency	fr	200	_	_	MHz	Vo==-20V , Ic=-50mA, f=100MHz
Output capacitance	Cob		_	8	pF	Vcs=-10V , f=100kHz
Emitter input capacitance	Cib		_	30	pF	V <sub>EB</sub> =-2V , f=100kHz
Turn-on time	ton	_	_	50	ns	Voc=-30V, Vee(off)=-1.5V, Ic=-150mA, Ie1=-15mA
Delay time	td	<b>—</b>	_	10	ns	Vcc=-30V , VBE(OFF)=-1.5V , Ic=-150mA , IB1=-15mA
Rise time	tr	_	-	40	ns	Vcc=-30V , VBE(OFF)=-1.5V , Ic=-150mA , IB1=-15mA
Turn-off time	toff	<u> </u>	T —	100	ns	Vcc=-30V , lc=-150mA , ls1=ls2=-15mA
Storage time	tstg		l –	80	ns	Vcc=-30V , lc=-150mA , ls1=ls2=-15mA
Fall time	tf	<del>  -</del>	_	30	ns	Vcc=-30V , lc=-150mA , le1=le2=-15mA

### Electrical characteristic curves

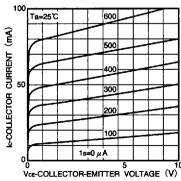


Fig.1 Grounded emitter output characteristics

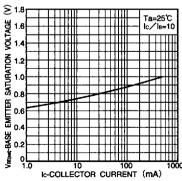


Fig.2 Base-emitter saturation voltage vs. collector current

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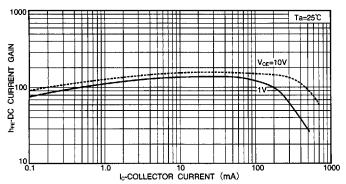


Fig.3 DC current gain vs. collector current (I)

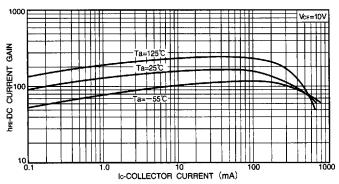


Fig.4 DC current gain vs. collector current (II)

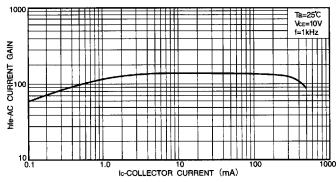
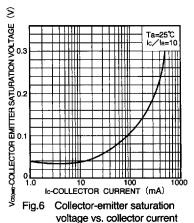


Fig.5 AC current gain vs. collector current



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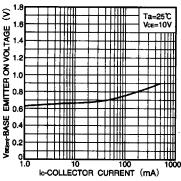
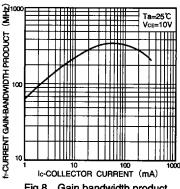


Fig.7 Grounded emitter propagation characteristics



Gain bandwidth product vs. collector current

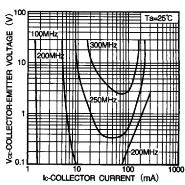
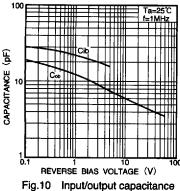


Fig.9 Gain bandwidth product



vs. voltage

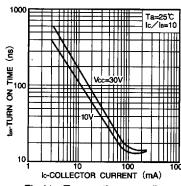


Fig.11 Turn-on time vs. collector current

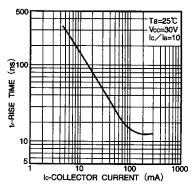


Fig.12 Rise time vs. collector current

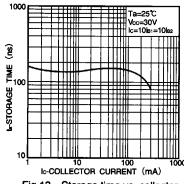
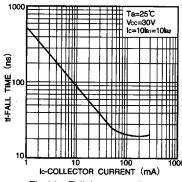


Fig.13 Storage time vs. collector current



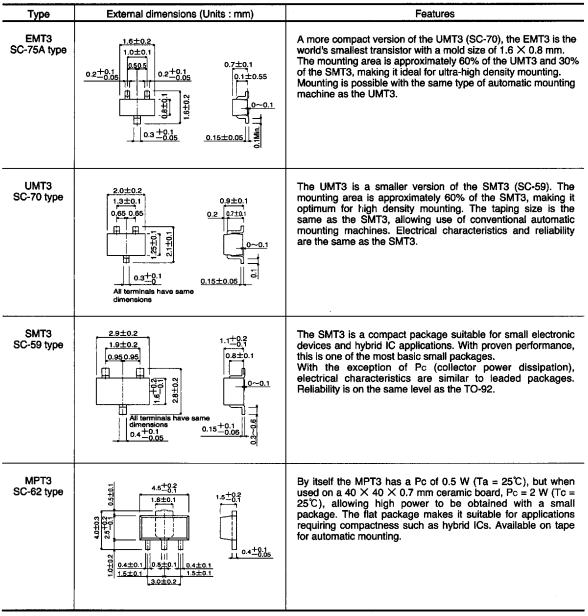
Fall time vs. collector current

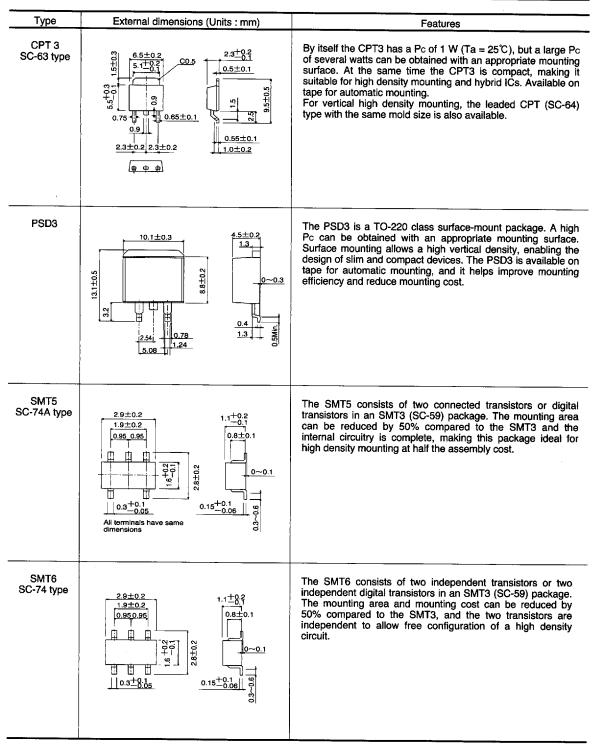
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## **Packages**

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.

Types and features of surface-mount packages

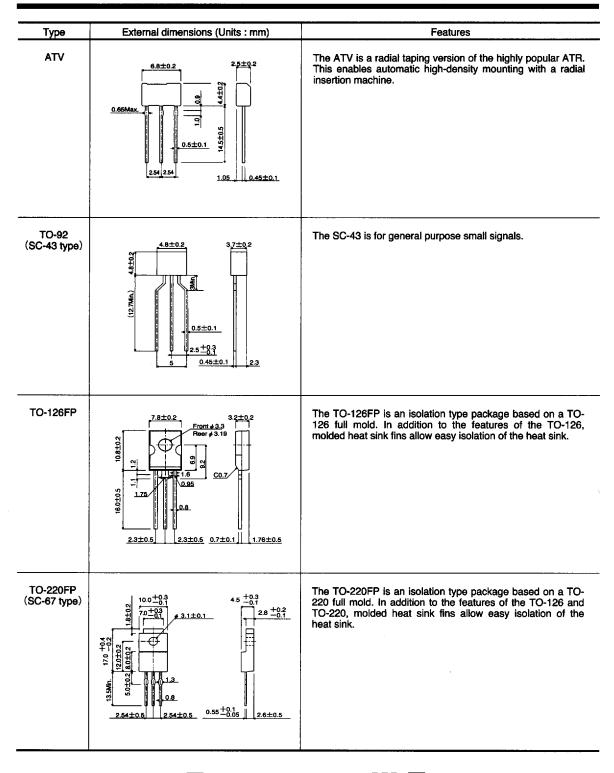




Туре	External dimensions (Units : mm)	Features
UMT5 SC-88A type	2.0±0.2 1,3±0.1 0,85 0,85 0,7 0,005 All terminals have same dimensions	The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost.
UMT6 SC-88 type	2.0±0.2 1,3±0.1 0.65 0.65 0.7 0.7 0.7 0.7 0.7 0.7 0.7 0.7	The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit.

## ●Types and features of leaded packages

Туре	External dimensions (Units : mm)	Features
SPT (SC-72 type)	2±0,2 0.45±0.15 0.45±0.15 0.5 0.45±0.15 0.5 0.45±0.15	The SPT is a smaller version of the conventional TO-92 type. The body size (3×4×2 mm³) has been reduced to 1/4 that of the TO-92 (5×5×4 mm³). The SPT is available on tape for automatic insertion, and less space is occupied on the printed circuit board than the TO-92. Reliability is the same as the TO-92.
FTR	0.65±0.1 2.4±0.2 0.55±0.1 0.55±0.1 0.45±0.1 0.45±0.1	SIL type with a height of 3.4 mm and a lead pitch of 2.54 mm.
FTL	0.65Max 2.4±0.2 0.65Max 2.4±0.2 0.5±0.1 0.5±0.1	The FTL is a radial taping version of the highly popular FTR. This enables automatic high-density mounting with a radial insertion machine.
ATR (SC-71 type)	0.65Max	SC-71type with a height of 4.4 mm and a Pc=1W type.



Type	External dimensions (Units : mm)	Features
TO-220FN	\$3.2±0.2	The TO-220FN features the same performance as the TO-220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short-circuiting problems with neighboring components and the chassis.  To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.